N-Channel Enhancement-Mode Vertical DMOS FETs

Features

- Free from secondary breakdown
- Low power drive requirement
- Ease of paralleling
- Low C_{ISS} and fast switching speeds
- Excellent thermal stability
- Integral SOURCE-DRAIN diode
- High input impedance and high gain
- Complementary N- and P-Channel devices

Applications

- Motor controls
- Converters
- Amplifiers
- Switches
- Power supply circuits
- Drivers (relays, hammers, solenoids, lamps, memories, displays, bipolar transistors, etc.)

General Description

The Supertex VN0550 is an enhancement-mode (normally-off) transistor that utilizes a vertical DMOS structure and Supertex's well-proven silicon-gate manufacturing process. This combination produces a device with the power handling capabilities of bipolar transistors, and the high input impedance and positive temperature coefficient inherent in MOS devices. Characteristic of all MOS structures, this device is free from thermal runaway and thermally-induced secondary breakdown.

Supertex's vertical DMOS FETs are ideally suited to a wide range of switching and amplifying applications where very low threshold voltage, high breakdown voltage, high input impedance, low input capacitance, and fast switching speeds are desired.

Ordering Information

Device	Package	BV_{DSS}/BV_{DGS} (V)	$R_{DS(ON)}$ (max) (Ω)	$I_{D(ON)}$ (min) (mA)
VN0550N3	TO-92	500	60	150
VN0550N3-G				

-G indicates package is RoHS compliant ('Green')

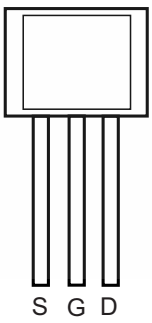
Absolute Maximum Ratings

Parameter	Value
Drain to source voltage	BV_{DSS}
Drain to gate voltage	BV_{DGS}
Gate to source voltage	±20V
Operating and storage temperature	-55°C to +150°C
Soldering temperature[1]	+300°C

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these conditions is not implied. Continuous operation of the device at the absolute rating level may affect device reliability. All voltages are referenced to device ground.

Notes:
1. Distance of 1.6mm from case for 10 seconds.

Pin Configuration



TO-92
(front view)

Electrical Characteristics (T_A = 25°C unless otherwise specified)

Symbol	Parameter	Min	Typ	Max	Units	Conditions
BV_{DSS}	Drain-to-source breakdown voltage	500	-	-	V	V_{GS} = 0V, I_D = 1.0mA
$V_{GS(th)}$	Gate threshold voltage	2.0	-	4.0	V	V_{GS} = V_{DS}, I_D = 1.0mA
$\Delta V_{GS(th)}$	Change in $V_{GS(th)}$ with temperature	-	-3.8	-5.0	mV/°C	V_{GS} = V_{DS}, I_D = 1.0mA
I_{GSS}	Gate body leakage current	-	-	100	nA	V_{GS} = ±20V, V_{DS} = 0V
I_{DSS}	Zero gate voltage drain current	-	-	10	µA	V_{GS} = 0V, V_{DS} = Max Rating
		-	-	1.0	mA	V_{GS} = 0V, V_{DS} = 0.8 Max Rating, T_A = 125°C
$I_{D(ON)}$	ON-state drain current	-	100	-	mA	V_{GS} = 5.0V, V_{DS} = 25V
		150	350	-		V_{GS} = 10V, V_{DS} = 25V
$R_{DS(ON)}$	Static drain-to-source ON-state resistance	-	45	-	Ω	V_{GS} = 5.0V, I_D = 50mA
		-	40	60		V_{GS} = 10V, I_D = 50mA
$\Delta R_{DS(ON)}$	Change in $R_{DS(ON)}$ with temperature	-	1.0	1.7	%/°C	V_{GS} = 10V, I_D = 50mA
G_{FS}	Forward transconductance	50	100	-	mmho	V_{DS} = 25V, I_D = 50mA
C_{ISS}	Input capacitance	-	45	55	pF	V_{GS} = 0V, V_{DS} = 25V, f = 1.0MHz
C_{OSS}	Common source output capacitance	-	8.0	10		
C_{RSS}	Reverse transfer capacitance	-	2.0	5.0		
$t_{d(ON)}$	Turn-ON time	-	-	10	ns	V_{DD} = 25V, I_D = 150mA, R_{GEN} = 25Ω
t_r	Rise time	-	-	15		
$t_{d(OFF)}$	Turn-OFF time	-	-	10		
t_f	Fall time	-		10		
V_{SD}	Diode forward voltage drop	-	0.8	-	V	V_{GS} = 0V, I_{SD} = 500mA
t_{rr}	Reverse recovery time	-	300	-	ns	V_{GS} = 0V, I_{SD} = 500mA

Notes:

1. All D.C. parameters 100% tested at 25°C unless otherwise stated. (Pulse test: 300µs pulse, 2% duty cycle.)

2. All A.C. parameters sample tested.

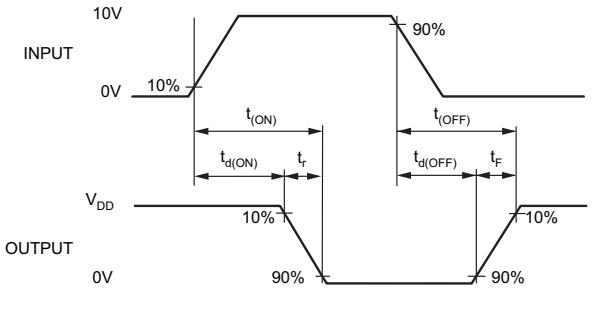
Thermal Characteristics

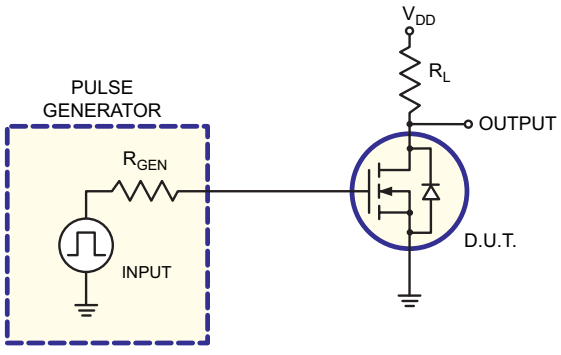
Device	Package	I_D (continuous)* (mA)	I_D (pulsed) (mA)	Power Dissipation @T_C = 25°C (W)	θ_{JC} (°C/W)	θ_{JA} (°C/W)	I_{DR}* (mA)	I_{DRM} (mA)
VN0550	TO-92	50	250	1.0	125	170	50	250

Notes:

* *I_D (continuous) is limited by max rated T_J.*

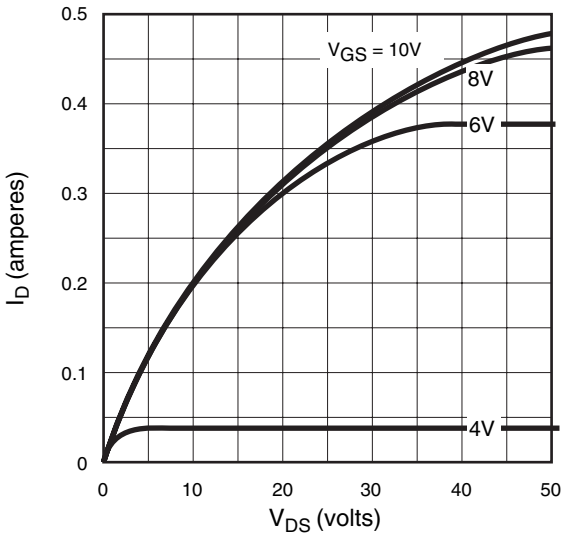
Switching Waveforms and Test Circuit



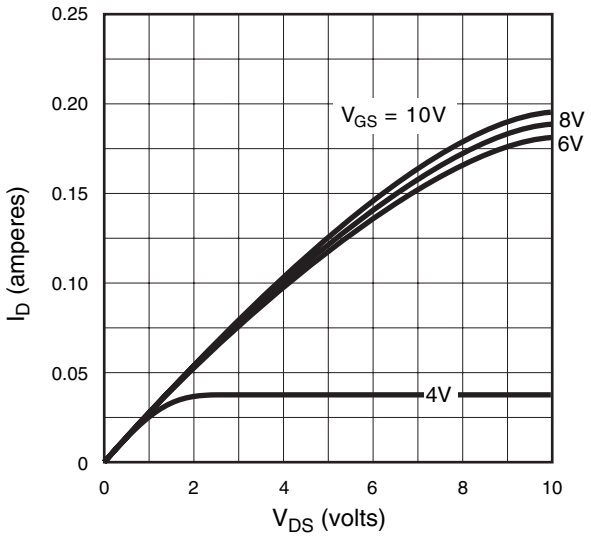


Typical Performance Curves

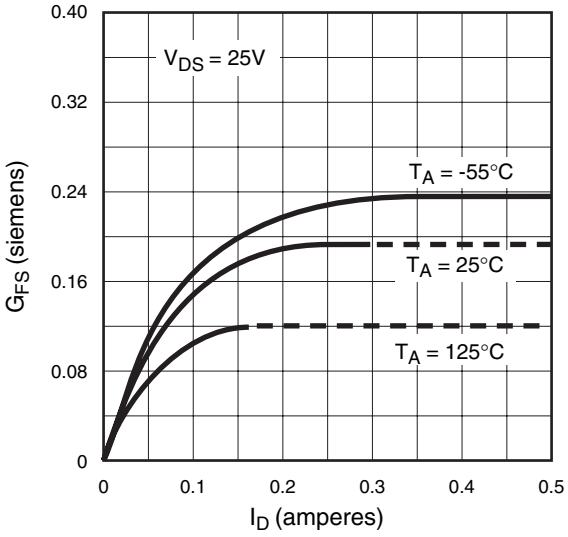
Output Characteristics



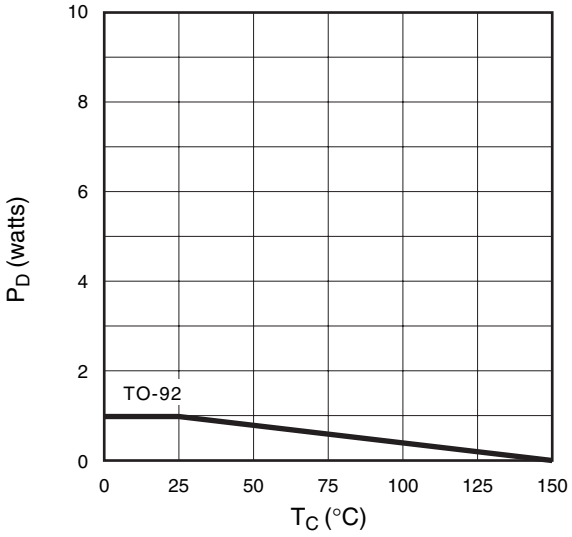
Saturation Characteristics



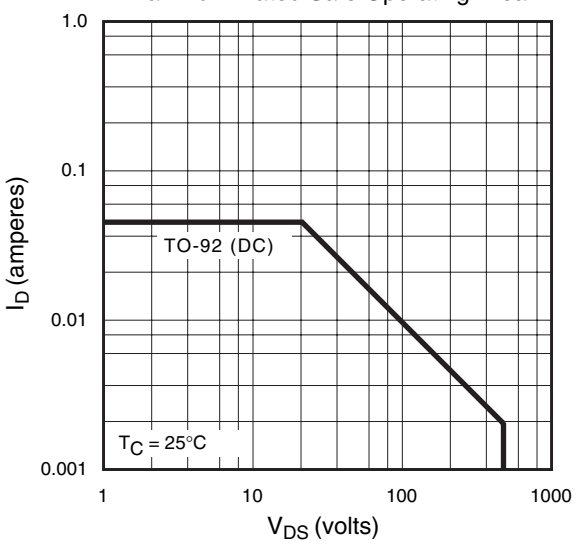
Transconductance vs. Drain Current



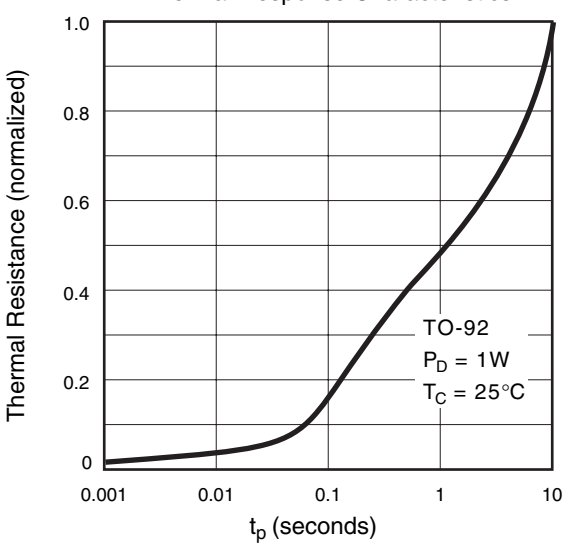
Power Dissipation vs. Case Temperature



Maximum Rated Safe Operating Area

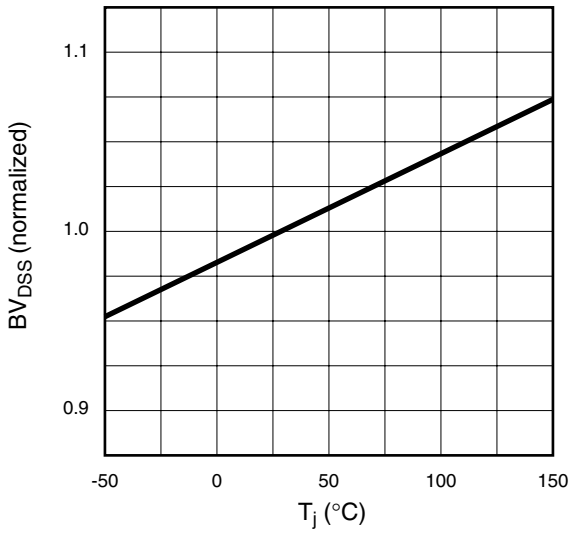


Thermal Response Characteristics

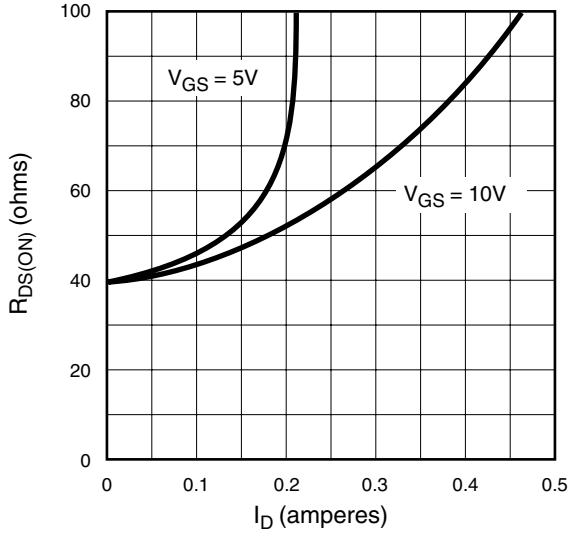


Typical Performance Curves *(cont.)*

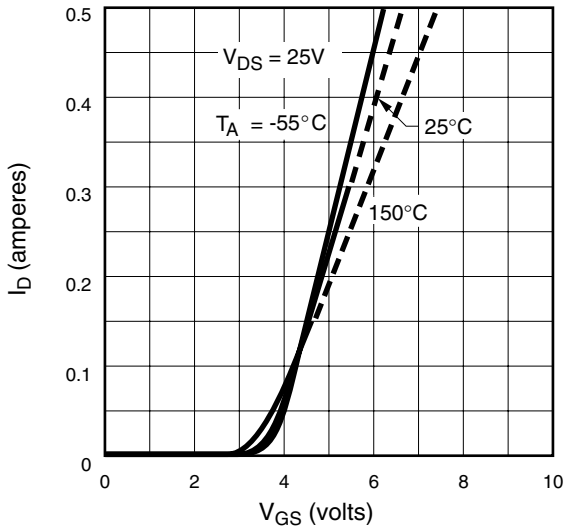
BV_{DSS} Variation with Temperature



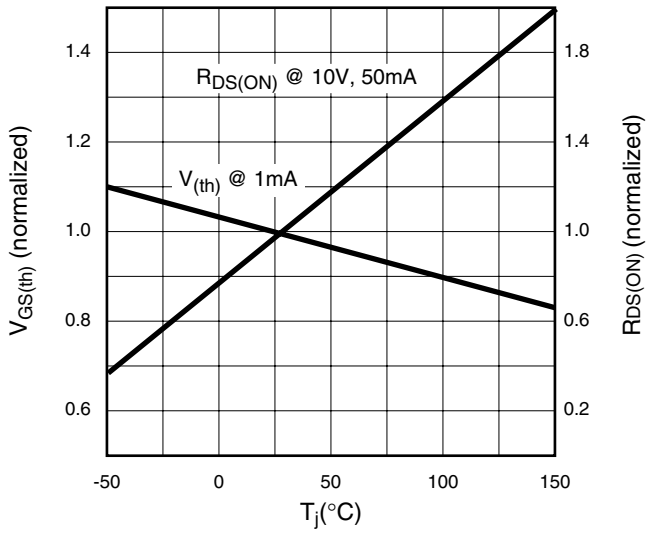
On-Resistance vs. Drain Current



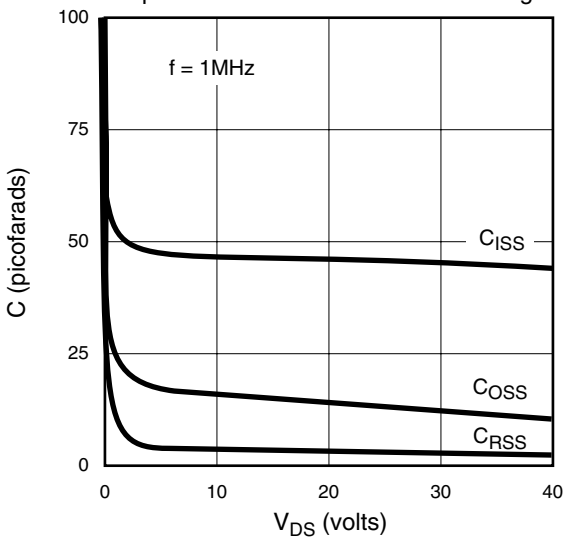
Transfer Characteristics



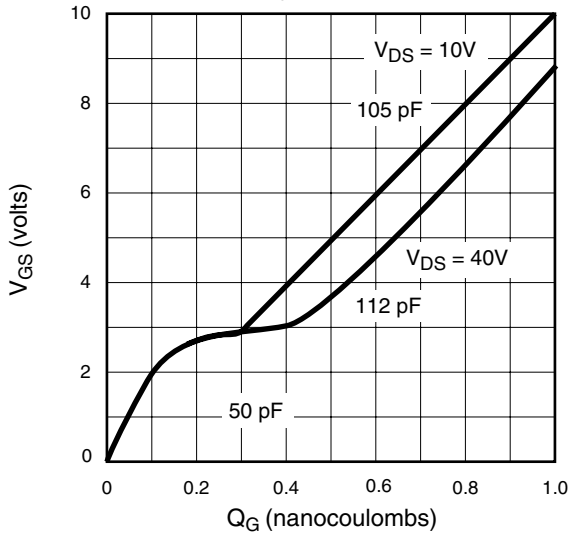
$V_{(th)}$ and R_{DS} Variation with Temperature



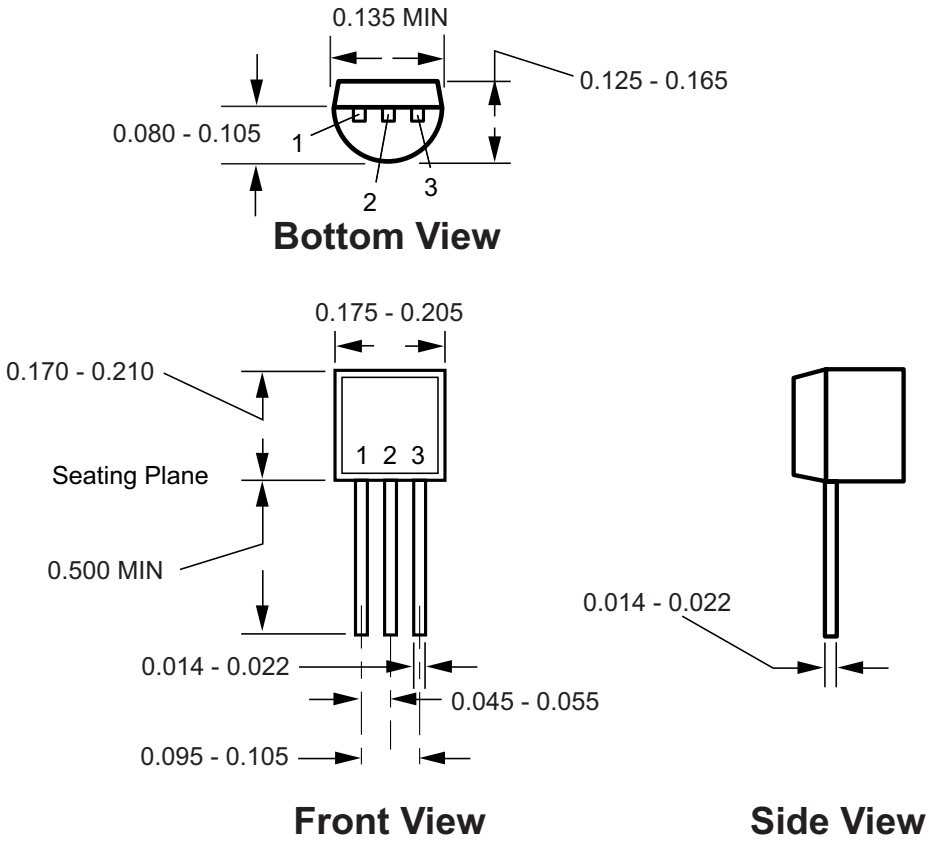
Capacitance vs. Drain-to-Source Voltage



Gate Drive Dynamic Characteristics



TO-92 Package Outline



Notes:
All dimensions are in millimeters; all angles in degrees.

(The package drawing(s) in this data sheet may not reflect the most current specifications. For the latest package outline information go to http://www.supertex.com/packaging.html.)

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